

GBAV70

Description

The GBAV70 consists of two diodes in a plastic surface mount package. The diodes are connected in series and the unit is designed for high-speed switching application in hybrid thick and thin-film circuits.

Package Dimensions

SOT-23

Diagram :

Marking:

Style : Pin1. Anode 2. Anode 3. Cathode

REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	1.90	REF.
B	2.40	2.80	H	1.00	1.30
C	1.40	1.60	K	0.10	0.20
D	0.35	0.50	J	0.40	-
E	0	0.10	L	0.85	1.15
F	0.45	0.55	M	0°	10°

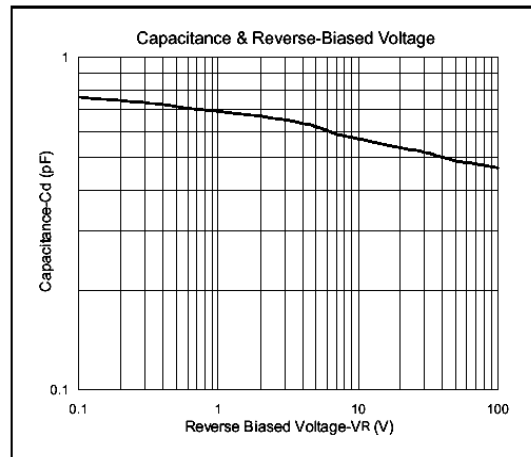
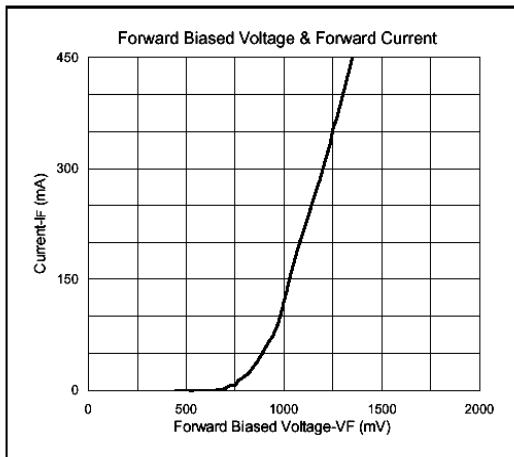
Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	T _j	+150	°C
Storage Temperature	T _{stg}	-65~+150	°C
Reverse Voltage		80	V
Forward Current		200	mA
Repetitive Forward Current		500	mA
Total Power Dissipation	PD	225	mW

Characteristics at Ta = 25°C

Characteristic	Symbol	Min.	Max.	Unit	Test Conditions
Reverse Breakdown Voltage	V(BR)	80	-	V	IR=100uA
Forward Voltage	VF(1)	-	715	mV	IF=1mA
	VF(2)	-	855	mV	IF=10mA
	VF(3)	-	1100	mV	IF=50mA
	VF(4)	-	1300	mV	IF=100mA
Reverse Current	IR	-	5	uA	VR=80V
Total Capacitance	CT		1.5	pF	VR=0, f=1MHz
Reverse Recovery Time	T _{rr}	-	15	nS	IF=IR=10mA, RL=100Ω measured at IR=1Ma, VR=5V

Characteristics Curve



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